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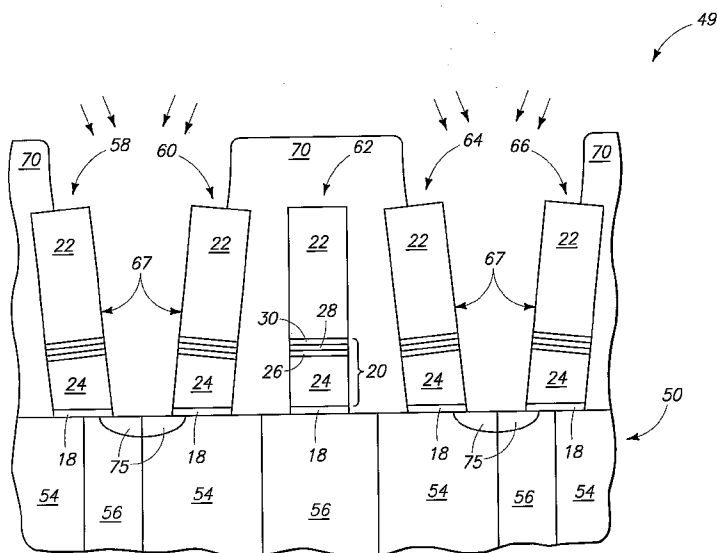
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(54) Title: ION IMPLANTING METHODS



(57) Abstract: An ion implanting method includes forming a pair of spaced and adjacent features projecting outwardly from a substrate. At least outermost portions of the pair of spaced features are laterally pulled away from one another with a patterned photoresist layer received over the features and which has an opening therein received intermediate the pair of spaced features. While such spaced features are laterally pulled, a species is ion implanted into substrate material which is received lower than the pair of spaced features. After the ion implanting, the patterned photoresist layer is removed from the substrate. Other aspects and implementations are contemplated.

WO 2007/001712 A1